

The silicon drift detector, data acquisition board, and detector power supply, which are required for X-ray absorption fine structure (XAFS) measurements used in material science structural analysis, have been integrated into one system. **By multi-elementing the silicon drift detectors with high counting rate and energy resolution, high sensitivity has been achieved.** Additionally, high-count measurements are made possible by properly performing transistor reset processing and DSP processing.

### Graphene Windowed Silicon Drift Detector

XSSD50-07GR

● **Total Sensitive Area: 329 mm<sup>2</sup>**  
(collimated to 47 mm<sup>2</sup> × 7 elements)

● **Total Element Area: 455 mm<sup>2</sup>**  
(65 mm<sup>2</sup> × 7 elements)



Tube length: 200 mm (default)

Detector back side

\*Modifications will incur additional costs.

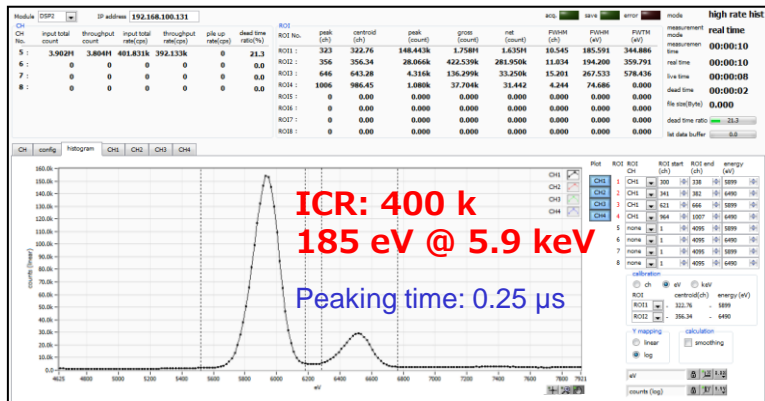


NIM-type  
**Detector power supply**  
APN3900  
1 unit

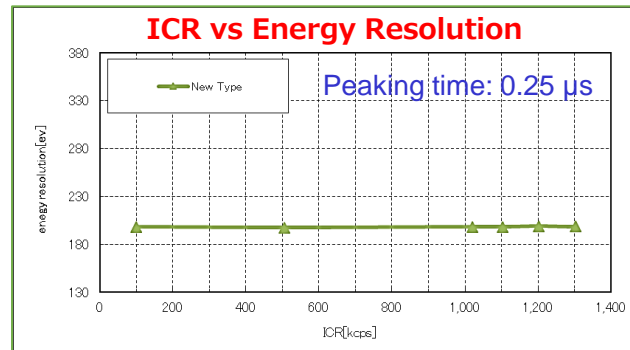


NIM-type  
**Measurement module**  
APN504X  
2 units

\*NIM bin power supply is required.

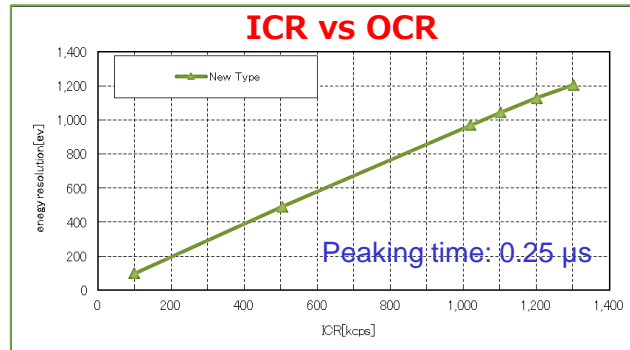


Screen of the included data collection application



### Specifications

Function	Histogram, List, Waveform, ROI-SCA
Energy resolution	244 eV @5.9 keV MnKa (OCR: 1000 k, Peaking time: 0.25μs)
ADC	100 MHz, 16-bit
Power supply for SDD	-200 V、±5V、+3.3V
Communication I/F	Gigabit Ethernet (TCP/IP)
Accessories	Data collection app, Sample program, User manual



\*Images is for illustration purpose.

\*Please note that contents may change without prior notice.

TechnoAP Co., Ltd.

2976-15 Mawatari, Hitachinaka, Ibaraki, Japan

Postcode:312-0012 [info@techno-ap.com](mailto:info@techno-ap.com)

TEL:+81-29-350-8011 FAX: +81-29-352-9013



<http://www.techno-ap.com>

20240313

